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ABSTRACT OF THE DISCLOSURE

GaN Single-Crystal Substrate, Nitride Type Semiconductor
Epitaxial Substrate, Nitride Type Semiconductor Device, And
Methods of Making the Same

The GaN single-crystal substrate 11 in accordance with the present invention has a polished surface subjected to heat treatment for at least 10 minutes at a substrate temperature of at least 1020°C in a mixed gas atmosphere containing at least an NH₃ gas. As a consequence, an atomic rearrangement is effected in the surface of the substrate 11 in which a large number of minute defects are formed by polishing, so as to flatten the surface of the substrate 11. Therefore, the surface of an epitaxial layer 12 formed on the substrate 11 can be made flat.